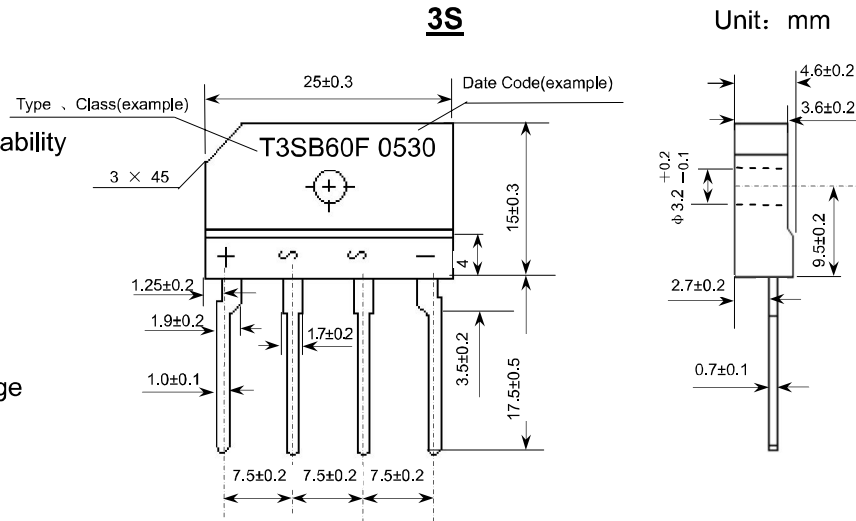


- I_o 4.0A
- V_{RRM} 200V~800V

- Glass passivated chip
- High surge forward current capability
- HF product

Applications

- General purpose 1 phase Bridge rectifier applications



Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	T3SB			
				20 F	40 F	60 F	80 F
Storage Temperature	T_{stg}	°C		-40 ~ +150			
Junction Temperature	T_j	°C		+150			
Repetitive Peak Reverse Voltage	V_{RRM}	V		200	400	600	800
Average Rectified Output Current	I_o	A	50Hz sine wave, R-load	4.0			
				2.3			
Surge(Non-repetitive)Forward Current	I_{FSM}	A	50Hz sine wave, 1 cycle, $T_a=25^{\circ}C$	120			
Current Squared Time	I^2t	A ² s	1ms ≤ t < 8.3ms $T_j=25^{\circ}C$, Rating of per diode	60			
Dielectric Strength	Vdis	kV	Terminals to case, AC 1 minute	2			
Mounting Torque	TOR	kg · cm	Recommend torque: 5kg · cm	8			

Electrical Characteristics ($T_a=25^{\circ}C$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	$I_{FM}=2.0A$, Pulse measurement, Rating of per diode	1.05
Peak Reverse Current	I_{RRM}	μ A	$V_{RM}=V_{RRM}$, Pulse measurement, Rating of per diode,	10
Thermal Resistance	$R_{\theta J-A}$	°C/W	Between junction and ambient, Without heatsink	30
	$R_{\theta J-L}$		Between junction and lead, Without heatsink	6
	$R_{\theta J-C}$		Between junction and case, With heatsink	5.5

■ Characteristics(Typical)

